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- Members of the Texas Instruments *Widebus*™ Family
- Universal Bus Transceiver (UBT[™]) Combines D-Type Latches and D-Type Flip-Flops for Operation in Transparent, Latched, Clocked, or Clock-Enabled Mode
- Translate Between GTL/GTL+ Signal Levels and LVTTL Logic Levels
- Support Mixed-Mode (3.3-V and 5-V) Signal Operation on A-Port and Control Inputs
- B-Port Transition Time Optimized for Distributed Backplane Loads
- I_{off} Supports Partial-Power-Down Mode Operation

- Bus Hold on A-Port Inputs Eliminates the Need for External Pullup/Pulldown Resistors
- Distributed V_{CC} and GND-Pin Configuration Minimizes High-Speed Switching Noise
- ESD Protection Exceeds JESD 22
 2000-V Human-Body Model (A114-A)
 200-V Machine Model (A115-A)
 - 1000-V Charged-Device Model (C101)
- Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II
- Package Options Include Plastic Shrink Small-Outline (DL), Thin Shrink Small-Outline (DGG), and Ceramic Flat (WD) Packages

description

The 'GTL16612A devices are 18-bit universal bus transceivers (UBT) that provide LVTTL-to-GTL+ and GTL+-to-LVTTL signal-level translation. They allow for transparent, latched, clocked, or clock-enabled modes of data transfer. These devices provide a high-speed interface between cards operating at LVTTL logic levels and backplanes operating at GTL+ signal levels. High-speed (about two times faster than standard LVTTL or TTL) backplane operation is a direct result of the reduced output swing (<1 V), reduced input threshold levels, and output edge control (OEC[™]). Improved GTL+ OEC circuits minimize bus settling time and have been designed and tested using several backplane models.

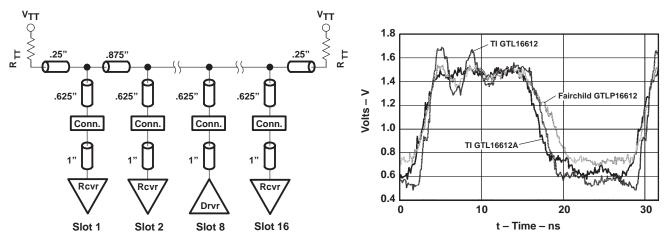


Figure 1. Test Backplane Model With Output Waveform Results



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description (continued)

Figure 1 shows actual device output waveforms using a synchronous clock at 75 MHz. The test backplane is a 16-slot, 14-inch board with loaded impedance of 33Ω . V_{TT} is 1.5 V, V_{REF} is 1 V, and R_{TT} pullup resistor is 50Ω . The driver is in slot 8, with receivers in alternate slots 1, 3, 5, 7, 10, 12, 14, and 16. Receiver slot 1 signals are shown. The signal becomes progressively worse as the receiver moves closer to the driver or the spacing between receiver cards is reduced. The clock is independent of the data and the system clock frequency is limited by the backplane flight time to about 80–90 MHz. This frequency can be increased even more (30% to 40%) if the clock is generated and transmitted together with the data off the driver card (source synchronous).

Additional design considerations can be found in Application Information at the end of this data sheet.

These 18-bit universal bus transceivers combine D-type latches and D-type flip-flops to allow data flow in transparent, latched, clocked, and clock-enabled modes. These UBTs can replace any of the functions shown in Table 1.

FUNCTION	8 BIT	9 BIT	10 BIT	16 BIT	18 BIT
Transceiver	'245, '623, '645	'863	'861	'16245, '16623	'16863
Buffer/driver	'241, '244, '541		'827	'827 '16241, '16244, '16541	
Latched transceiver	'543	'16543		'16472	
Latch	'373, '573	'843	'841	'16373	'16843
Registered transceiver	'646, '652			'16646, '16652	'16474
Flip-flop	'374, '574		'821	'16374	
Standard UBT					'16500, '16501
Universal bus driver					'16835
Registered transceiver with CLK enable	'2952			'16470, '16952	
Flip-flop with CLK enable	'377	'823			'16823
Standard UBT with CLK enable					'16600, '16601
'GTL	16612A UBT replaces	s all above	functions		

Table 1. 'GTL16612A UBT Replacement Functions

GTL+ is the Texas Instruments (TITM) derivative of the Gunning transceiver logic (GTL) JEDEC standard JESD 8-3. The AC specification of the 'GTL16612A is given only at the preferred higher noise margin GTL+, but this device can be used at either GTL ($V_{TT} = 1.2$ V and $V_{REF} = 0.8$ V) or GTL+ ($V_{TT} = 1.5$ V and $V_{REF} = 1$ V) signal levels.

The B port normally operates at GTL or GTL+ levels, while the A-port and control inputs are compatible with LVTTL logic levels and are 5-V tolerant. V_{REF} is the reference input voltage for the B port.

To improve signal integrity, the 'GTL16612A B-port output transition time is optimized for distributed backplane loads.

V_{CC} (5 V) supplies the internal and GTL circuitry, while V_{CC} (3.3 V) supplies the LVTTL output buffers.

Data flow in each direction is controlled by output-enable (OEAB and OEBA), latch-enable (LEAB and LEBA), and clock (CLKAB and CLKBA) inputs. The clock or latch enable can be controlled by the clock-enable (CEAB and CEBA) inputs. For A-to-B data flow, the devices operate in the transparent mode when LEAB is high. When LEAB is low, the A data is latched if CEAB is low and CLKAB is held at a high or low logic level. If LEAB is low, the A data is stored in the latch/flip-flop on the low-to-high transition of CLKAB if CEAB also is low. When OEAB is low, the outputs are active. When OEAB is high, the outputs are in the high-impedance state. Data flow for B to A is similar to that for A to B, but uses OEBA, LEBA, CLKBA, and CEBA.

To ensure the high-impedance state during power up or power down, \overline{OE} should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.



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description (continued)

Active bus-hold circuitry holds unused or undriven LVTTL inputs at a valid logic state. Use of pullup or pulldown resistors with the bus-hold circuitry is not recommended.

These devices are fully specified for partial-power-down applications using I_{off}. The I_{off} circuitry disables the outputs, preventing damaging current backflow through the devices when they are powered down.

The SN54GTL16612A is characterized for operation over the full military temperature range of -55° C to 125° C. The SN74GTL16612A is characterized for operation from -40° C to 85° C.

SN54GTL16612A . . . WD PACKAGE

	(TOP VI	G OR DL PACKAGE EW)
OEAB LEAB A1 GND A2 A3 V _{CC} (3.3 V) A4 A5 A6 GND A7 A8	4 5 7 8 9 10 11 12	56 CEAB 55 CLKAB 54 B1 53 GND 52 B2 51 B3 50 V _{CC} (5 V) 49 B4 48 B5 47 B6 46 GND 45 B7 44 B8
A9 [A10] A11] A12] GND [A13] A13] A14] A15] V _{CC} (3.3 V) [A16] A17] GND [A18] OEBA]	14 15 16 17 18 19 20 21 22 23 23 24	 44 43 43 44 44 45 44 45 44 46 41 40 41 42 41 42 41 41 42 41 41 42 41 42 44 44 44 44 <

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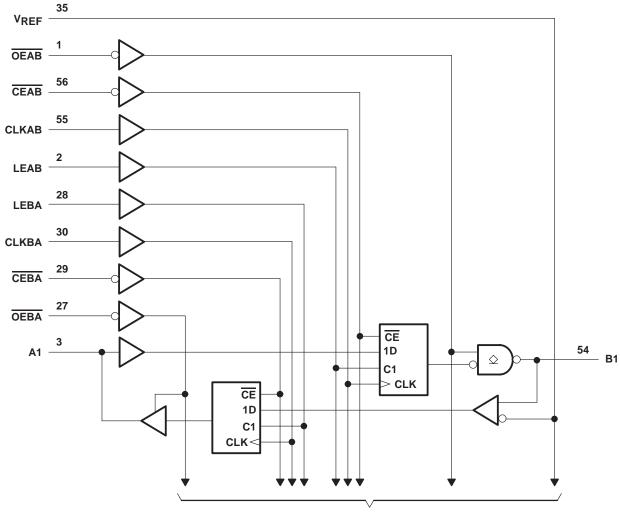
	FUNCTION TABLE [†]										
		INPUTS			OUTPUT	MODE					
CEAB	OEAB	LEAB	CLKAB	Α	В	MODE					
Х	Н	Х	Х	Х	Z	Isolation					
L	L	L	Н	Х	в ₀ ‡ в ₀ §	Latched storage of A data					
L	L	L	L	Х	в ₀ §	Latened Storage of A data					
Х	L	Н	Х	L	L	Transparent					
X	L	Н	Х	Н	н	Transparent					
L	L	L	\uparrow	L	L	Clocked storage of A data					
L	L	L	\uparrow	Н	н	CIUCKEU SIULAYE ULA UALA					
Н	L	L	Х	Х	в ₀ §	Clock inhibit					

[†] A-to-B data flow is shown. B-to-A data flow is similar, but uses OEBA, LEBA, CLKBA, and CEBA.

[‡]Output level before the indicated steady-state input conditions were established, provided that CLKAB was high before LEAB went low

§ Output level before the indicated steady-state input conditions were established

logic diagram (positive logic)



To 17 Other Channels



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absolute maximum ratings over operating free-air temperature range (unless otherwise noted)[†]

Supply voltage range, V _{CC} : 3.3 V	
Input voltage range, V _I (see Note 1): A-port and control inputs B port and V _{RFF}	\ldots –0.5 V to 7 V
Voltage range applied to any output in the high or power-off state, V_{Ω}	
(see Note 1): A port	–0.5 V to 7 V
B port	–0.5 V to 4.6 V
Current into any output in the low state, I _O : A port	
B port	80 mA
Current into any A-port output in the high state, I _O (see Note 2)	64 mA
Continuous current through each V _{CC} or GND	±100 mA
Input clamp current, I _{IK} (V _I < 0)	
Output clamp current, I _{OK} (V _O < 0)	
Package thermal impedance, θ _{JA} (see Note 3): DGG package	64°C/W
DL package	
Storage temperature range, T _{stg}	–65°C to 150°C

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

2. This current flows only when the output is in the high state and $V_O > V_{CC}$.

3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Notes 4 through 6)

			SNS	54GTL16612	2A	SN7	4GTL16612	2A	LINUT	
			MIN	NOM	MAX	MIN	NOM	MAX	UNIT	
	Cumphonetter	3.3 V	3.15	3.3	3.45	3.15	3.3	3.45	v	
VCC	Supply voltage	5 V	4.75	5	5.25	4.75	5	5.25	v	
\/	Termination voltage	GTL	1.14	1.2	1.26	1.14	1.2	1.26	v	
VTT	Termination voltage	GTL+	1.35	1.5	1.65	1.35	1.5	1.65	v	
\/	Cupply voltogo	GTL	0.74	0.8	0.87	0.74	0.8	0.87	v	
VREF	Supply voltage	GTL+	0.87	1	1.1	0.87	1	1.1	v	
V _I Ir	Input voltage	B port		Ē	VTT			VTT	v	
		Except B port		E	5.5			5.5	v	
Maria	High-level	B port	V _{REF} +50 mV	2		V _{REF} +50 mV			v	
VIH	input voltage	Except B port	2	(j)		2			v	
\/	Low-level	B port		2 V	/REF-50 mV		١	/REF-50 mV	v	
VIL	input voltage	Except B port	4	r r	0.8			0.8	v	
Iк	Input clamp current	-		7	-18			-18	mA	
IOH	High-level output current	A port			-32			-32	mA	
	Low-level	A port			64			64		
IOL	output current	B port			34			34	mA	
T _A	Operating free-air ter	mperature	-55		125	-40	-	85	°C	

NOTES: 4. All unused control inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

5. Normal connection sequence is GND first, $V_{CC} = 5 V$ second, and $V_{CC} = 3.3 V$, I/O, control inputs, V_{TT} , and V_{REF} (any order) last. 6. V_{TT} and R_{TT} can be adjusted to accommodate backplane impedances as long as they do not exceed the DC absolute I_{OL} ratings.

Similarly, $V_{\mbox{\scriptsize REF}}$ can be adjusted to optimize noise margins, but normally is 2/3 V_{\mbox{\scriptsize TT}}.



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electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

	AETED	TEST CONDIT	IONE	SN540	STL1661	2 A	SN740	STL1661	2 A		
PARAN	NEIER	TEST CONDIT	IONS	ΜΙΝ ΤΥΡ [†] ΜΑΧ			MIN	түр†	MAX		
VIK		V _{CC} (3.3 V) = 3.15 V, V _{CC} (5 V) = 4.75 V	Ij = -18 mA	nA –1.2		-1.2	V				
		V_{CC} (3.3 V) = 3.15 V to 3.45 V, V_{CC} (5 V) = 4.75 V to 5.25 V	I _{OH} = -100 μA	V _{CC} (3.3 V)–0.2			V _{CC} (3.3 V)–0.2				
Vон	A port	V _{CC} (3.3 V) = 3.15 V,	I _{OH} = -8 mA	2.4			2.4			V	
		V _{CC} (5 V) = 4.75 V	I _{OH} = -32 mA	2			2				
			I _{OL} = 100 μA			0.2			0.2		
	A port	V _{CC} (3.3 V) = 3.15 V,	I _{OL} = 16 mA			0.4			0.4		
VOL	/ poir	V _{CC} (5 V) = 4.75 V	I _{OL} = 32 mA			0.5			0.5	V	
			I _{OL} = 64 mA			0.6			0.55		
	B port	V_{CC} (3.3 V) = 3.15 V, V_{CC} (5 V)	= 4.75 V, I _{OL} = 34 mA			0.65			0.65		
	Control inputs	V_{CC} (3.3 V) = 0 or 3.45 V, V_{CC} (5 V) = 0 or 5.25 V	V _I = 5.5 V			10			10		
			V _I = 5.5 V			1000			20		
lı	A port	V _{CC} (3.3 V) = 3.45 V, V _{CC} (5 V) = 5.25 V	VI = VCC (3.3 V)			1			1	μA	
-			$V_{I} = 0$		Ìn.	-30			-30		
Rpg	Deart	V_{CC} (3.3 V) = 3.45 V,	$V_{I} = V_{CC} (3.3 V)$		VIE VIE	5			5		
	B port	V _{CC} (5 V) = 5.25 V	V _I = 0		2	-5	-5		-5	1	
loff		$V_{CC} = 0,$	$V_{I} \text{ or } V_{O} = 0 \text{ to } 4.5 \text{ V}$		~	1000			100	μ	
		port $V_{CC} (3.3 V) = 3.15 V,$ $V_{CC} (5 V) = 4.75 V$	V _I = 0.8 V	75	5		75				
ll(hold)	A port		V _I = 2 V	-75			-75			μ/	
			$V_{I} = 0$ to $V_{CC} (3.3 V)^{\ddagger}$	Q		±500			±500	1	
IOZH	A port	V _{CC} (3.3 V) = 3.45 V, V _{CC} (5 V) = 5.25 V	$V_{O} = V_{CC} (3.3 V)$			1			1	μ/	
	B port	V _{CC} (3.3 V) = 3.45 V, V _{CC} (5 V)	= 5.25 V, V _O = 1.5 V			10			10		
1	A port	V _{CC} (3.3 V) = 3.45 V, V _{CC} (5 V)	= 5.25 V, V _O = 0			-1			-1		
IOZL	B port	V _{CC} (3.3 V) = 3.45 V, V _{CC} (5 V)	= 5.25 V, V _O = 0.65 V			-10			-10	μ	
		V _{CC} (3.3 V) = 3.45 V,	Outputs high			1			1		
ICC (3.3 V)	A or B port	V_{CC} (5 V) = 5.25 V, I _O = 0, V _I = V _{CC} (3.3 V) or GND§,	Outputs low			5			5	m	
(0.0 v)	pon	$V_{I} = V_{TT} \text{ or } GND^{\P}$	Outputs disabled			1		$(3.3 \vee)-0.2$ 2.4 2 0.2 0.2 0.4 0.4 0.5 0.55 0.65 0.65 10 20 1 1 -30 5 -5 100 75 -5 100 75 -75 ±500 1 1 1 10 -10 -10 -10 1			
		V _{CC} (3.3 V) = 3.45 V,	Outputs high			120			120		
ICC	A or B V_{CC} (5 V) = 5.25 V, I_{C} = 0,		Outputs low			120			120	m	
(5 V) port $V_{I} = V_{CC} (3.3 V) \text{ or } GND\$$, Outputs low $V_{I} = V_{TT} \text{ or } GND\P$ Outputs disabled			120				1				
∆I _{CC} (3.	.3 V)#	V_{CC} (3.3 V) = 3.45 V, V_{CC} (5 V) One A-port or control input at 2.7 Other A-port or control inputs at V	= 5.25 V, V,			1				m	
Ci	Control inputs	V _I = 3.15 V or 0			4	12		4		pF	
Cia	A port	V _O = 3.15 V or 0			8.5	18		8.5		pf	
Cio	B port	V _O = 1.5 V or 0				10		8		l ^{pr}	

[†] All typical values are at V_{CC} (3.3 V) = 3.3 V, V_{CC} (5 V) = 5 V, T_A = 25°C.

[‡]This is the bus-hold maximum dynamic current. It is the minimum overdrive current required to switch the input from one state to another. § This is the V_I for A-port or control inputs.

This is the V_I for B port.

[#]This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

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timing requirements over recommended ranges of supply voltage and operating free-air temperature, V_{TT} = 1.5 V and V_{REF} = 1 V for GTL+ (unless otherwise noted) (see Figure 2)

			SN54GTL	16612A	SN74GTL1	6612A	UNIT		
			MIN	MAX	MIN	MAX	UNIT		
fclock	Clock frequency			85		85	MHz		
+	Pulse duration	LEAB or LEBA high	3.3		3.3		ns		
tw		CLKAB or CLKBA high or low	5.7		5.7		115		
		A before CLKAB↑	1		1				
		B before CLKBA↑	2.7	Mi	1.8				
	Cotup time	A before LEAB \downarrow	1.7	N.	0.5				
t _{su}	Setup time	B before LEBA \downarrow	1.2	27	1.2		ns		
		CEAB before CLKAB↑	<ab↑ 1.3<="" td=""><td>1.2</td><td></td><td colspan="2"></td></ab↑>		1.2				
		CEBA before CLKBA↑	BA before CLKBA1						
		A after CLKAB↑	3.2		1.9				
		B after CLKBA↑	4.3		0.5				
		A after LEAB↓	3.2		2.7				
t _h Hold time		B after LEBA \downarrow	4.2		3.5		ns		
		CEAB after CLKAB↑	2.4		1.2				
		CEBA after CLKBA↑	1.1		1.1				

switching characteristics over recommended ranges of supply voltage and operating free-air temperature, V_{TT} = 1.5 V and V_{REF} = 1 V for GTL+ (see Figure 2)

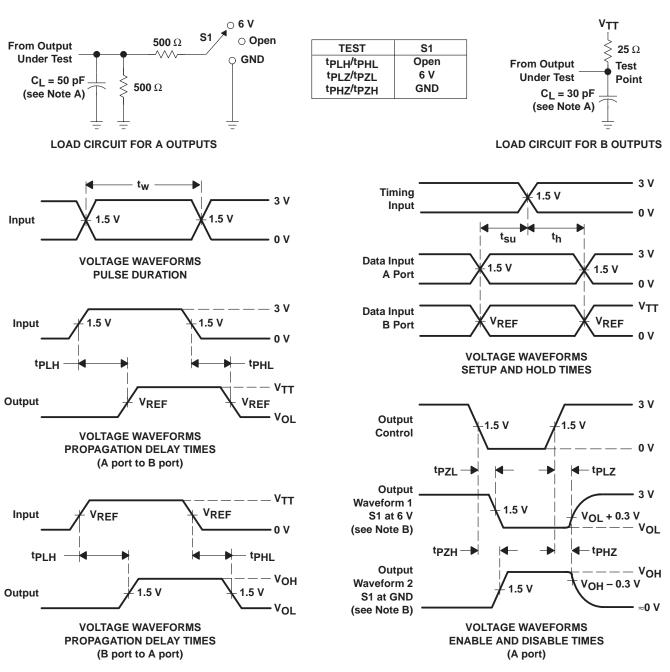
DADAMETED	FROM TO		SN54	GTL166	12A	SN74GTL16612A				
PARAMETER	(INPUT)	(OUTPUT)	MIN	түр†	MAX	MIN	TYP [†]	MAX	UNIT	
f _{max}			85			85			MHz	
^t PLH	А	В	2		7.3	2.5		6.9	ns	
^t PHL	A	D	2.2		7.4	2.5		6.9	115	
^t PLH	LEAB	В	2.2		7.5	3.2		7.3	ns	
^t PHL	LEAD	D	2.3		7.9	3.2		7.3	115	
^t PLH	OLIKAD	В	2.1		8	3.4		7.8		
^t PHL	CLKAB		2.5	4	7.9	3.4		7.8	ns	
t _{en}	OEAB	В	1.8	E	7.4	2.8		7	ns	
^t dis			1.8	2	7	2.8		7		
tr	Transition time, B ou	sition time, B outputs (20% to 80%)			2.6			2.6		
t _f	Transition time, B ou	utputs (80% to 20%)		2.6			2.6		ns	
^t PLH	В				6.3	1.5		5.7		
^t PHL	D	A	1.3		6.2	1.5		5.7	ns	
^t PLH	LEBA	А	1.5		6.1	1.8		5.7		
^t PHL	LEDA	A	1		6	1.8		5.7	ns	
^t PLH		Δ	1.8		5.8	2.3		5.5		
^t PHL	CLKBA	A	2		5.9	2.3		5.5	ns	
t _{en}	OEBA	Δ.	0.5		6.2	1.8		6.1		
t _{dis}	UEDA	A	1.3		6.6	1.8		6.1	ns	

[†] All typical values are at V_{CC} (3.3 V) = 3.3 V, V_{CC} (5 V) = 5 V, T_A = 25°C.

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PARAMETER MEASUREMENT INFORMATION

NOTES: A. CL includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, Z_O = 50 Ω , t_f \leq 2.5 ns. t_f \leq 2.5 ns.
- D. The outputs are measured one at a time with one transition per measurement.

Figure 2. Load Circuits and Voltage Waveforms



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APPLICATION INFORMATION

GTL background information

GTL was approved as JEDEC standard JESD 8-3 in 1993 and originally was created as a reduced-swing I/O driver technology to support high-speed buses and backplanes. The GTL bus is designed to work with low voltage swings. The input buffer works like an analog comparator rather than like an inverter, which allows the GTL inputs to switch quickly without needing to be driven rail to rail. GTL drivers were designed to pull a 1.2-V signal down to 0.4 V when switched on. This, however, placed the reference voltage for the input comparator at 0.8 V, which made it susceptible to ground-bounce noise. A variant of GTL, called GTL+, is being used to address this noise-margin concern. The GTL+ termination voltage is raised to 1.5 V, with the driver pulling down to a V_{OL} of 0.5 V. This moved the reference voltage to 1 V and out of the range of most ground bounces.

TI GTL devices operate at, and are specified for, both GTL and the improved-noise-margin GTL+ standard. However, the 'GTL16612A devices deviate from this history. They are designed with slow rising and falling edges, to offer significant system frequency improvement in heavily loaded backplanes. They are AC specified only at GTL+ because most applications are moving to this improved-noise-margin standard; they operate at either GTL or GTL+.

Devices named GTL or GTLP indicate reduced voltage-swing operation at a V_{TT} of 1.2 V (GTL standard) or 1.5 V (improved-noise-margin GTL+ standard). Fast-edge GTL devices are best for point-to-point or lower-frequency backplanes. Slow-edge GTL devices extend backplane operations to cover even higher frequencies.

input characteristics

The input characteristics are identical on both A and B ports. Both ports are very high impedance and have an input diode to provide protection against high negative-voltage spikes. The input diode conducts and prevents more sensitive components from being destroyed as the result of electrostatic discharges or line reflections.

GTL output characteristics

The principle of the GTL bus is based on open-drain drivers, as shown in Figure 3.

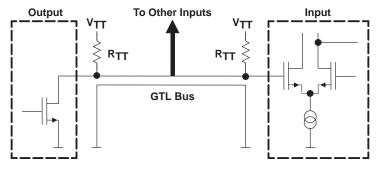


Figure 3. GTL Bus: An Open-Drain Bus

The devices actively drive the bus low, whereas, the termination voltage source, V_{TT} pulls it high. Only the pullup resistor (R_{TT}), which usually is of a low resistance, limits the current. The pullup resistor value should match the fully loaded backplane impedance, not the trace impedance, to provide an optimum termination of the bus and avoid line reflections. The resistance of the GTL output is in the range of a few ohms. However, in the high state, the output transistor is in the high-impedance state. R_{TT} needs to be greater than 25 Ω at GTL+ signal levels, not to exceed the 'GTL16612A absolute maximum output current of 80 mA, and should be greater than 50 Ω at GTL+ signal levels, not to exceed the recommended output current limit of 34 mA.



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APPLICATION INFORMATION

OEC

The 'GTL16612A GTL output consists of an improved edge-control circuit that provides optimized rise and fall times, typically 2.6 ns (20% to 80%), for backplanes under various loading conditions.

Using the definition of slew rate $\Delta t/\Delta v = t_r \text{ or } t_f/(V_{OH} - V_{OL})$, the slew rate of the device typically is 5 ns/V. As a comparison, these values are significantly more than those of previous GTL or standard TTL devices, which are usually about 1 ns/V, or less.

termination voltage, V_{TT}

The termination voltage (V_{TT}) should be derived from a voltage regulator that can provide up to 50-mA current per signal line. There are various voltage regulators that meet these requirements. Depending on the application, the regulators should be mounted either directly on the backplane or on the daughter boards. It is highly recommended that ceramic bypass capacitors be used (due to high impedance) at the termination resistors because several signal lines may be switching simultaneously, causing considerable current fluctuations at the termination voltage.

reference voltage, V_{REF}

The GTL reference voltage (V_{REF}) can be derived using a simple voltage divider between V_{TT} and GND with an R-to-2R ratio and a bypass capacitor (0.01–0.1 μ F) as close to the V_{REF} terminal as possible (see Figure 4). Generating V_{REF} from V_{TT} ensures the maximum possible signal-to-noise ratio (SNR) even with an unstable termination voltage. It also is recommended to generate V_{REF} locally on each plug-in card instead of on the backplane.

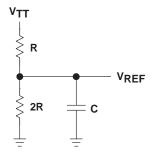


Figure 4. Suggested Connection of V_{REF} Terminal

partial power down

Device power can be switched off without having to remove the device from the system. This is a partial power down. 'GTL16612A can be used in a partial-power-down application where $V_{CC} = 0$ because the inputs and outputs are at high impedance and are able to tolerate active bus signals. This is reflected in the I_{off} parameter, which specifies the maximum input or output leakage current.

bus-hold circuit

Bus hold on A-port inputs (LVTTL side) prevents any unused or floating inputs from damaging the device. To change the logic state stored by the bus-hold circuit, a current of about 250–300 μ A must be overridden. There is no bus hold on the B port (GTL side). A bus-hold circuit on the GTL side would defeat the purpose of the open-drain outputs, which take on the high-impedance state to allow the bus to achieve a logic high state via the pullup resistors.



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APPLICATION INFORMATION

source-synchronous clock applications

When the clock originates at the driver card and is carried out with the data, the backplane maximum frequency can be achieved. This is possible because the backplane flight time no longer is the limiting factor.

Figure 5 shows results of the 'GTL16612A operating at 100 MHz in a source-synchronous mode.

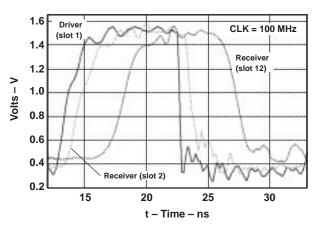


Figure 5. Source-Synchronous Clock

summary

'GTL16612A devices provide significant benefits when designing high-speed parallel backplanes.

- B port specifically optimized for distributed backplane levels
- Improved B-port GTL edge-control circuitry provides better signal integrity at higher frequencies.
- Reduced power consumption over BTL technology
- Similar to 'LVTH16601, with the B port operating at GTL+ signal levels
- Data throughput is 1.35 Gbit/s at 75-MHz clock speed.
- Provide about two times the data throughput over existing TTL devices, using existing parallel backplane designs

Additional information on GTL devices and backplane design considerations can be found at http://www.ti.com/sc/gtl.



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